

Switch-mode Schottky Power Rectifier

MBRF2020CTG

The Switch-mode Power Rectifier employs the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for use as rectifiers in very low-voltage, high-frequency switching power supplies, free wheeling diodes and polarity protection diodes.

Features

- Highly Stable Oxide Passivated Junction
- Very Low Forward Voltage Drop
- Matched Dual Die Construction
- High Junction Temperature Capability
- High dv/dt Capability
- Guardring for Stress Protection
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Electrically Isolated. No Isolation Hardware Required.
- These Devices are Pb-Free and are RoHS Compliant

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

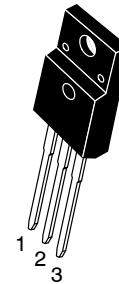
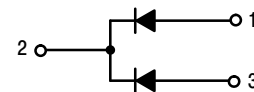
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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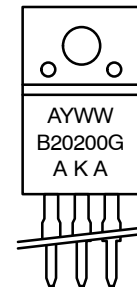
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SCHOTTKY BARRIER RECTIFIER 20 AMPERES, 200 VOLTS



TO-220 FULLPAK™
CASE 221D

MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- WW = Work Week
- B2020G = Device Code
- G = Pb-Free Package
- AKA = Polarity Designator

ORDERING INFORMATION

Device	Package	Shipping
MBRF2020CTG	TO-220 (Pb-Free)	50 Units/Rail

MBRF20200CTG

MAXIMUM RATINGS (Per Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	200	V
Average Rectified Forward Current (Rated V_R) $T_C = 125^\circ\text{C}$	$I_{F(AV)}$	10 20	A Per Leg Per Package
Peak Repetitive Forward Current, Per Leg (Rated V_R , Square Wave, 20 kHz) $T_C = 90^\circ\text{C}$	I_{FRM}	20	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	150	A
Peak Repetitive Reverse Surge Current (2.0 μs , 1.0 kHz)	I_{RRM}	1.0	A
Operating Junction Temperature and Storage Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/ μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (Per Leg)

Rating	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.5	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS (Per Leg)

Rating	Symbol	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1) ($i_F = 10$ Amp, $T_C = 25^\circ\text{C}$) ($i_F = 10$ Amp, $T_C = 125^\circ\text{C}$) ($i_F = 20$ Amp, $T_C = 25^\circ\text{C}$) ($i_F = 20$ Amp, $T_C = 125^\circ\text{C}$)	V_F	0.9 0.8 1.0 0.9	V
Maximum Instantaneous Reverse Current (Note 1) (Rated dc Voltage, $T_C = 25^\circ\text{C}$) (Rated dc Voltage, $T_C = 125^\circ\text{C}$)	i_R	1.0 50	mA

DYNAMIC CHARACTERISTICS (Per Leg)

Capacitance ($V_R = -5.0$ V, $T_C = 25^\circ\text{C}$, Freq. = 1.0 MHz)	C_T	500	pF
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1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$

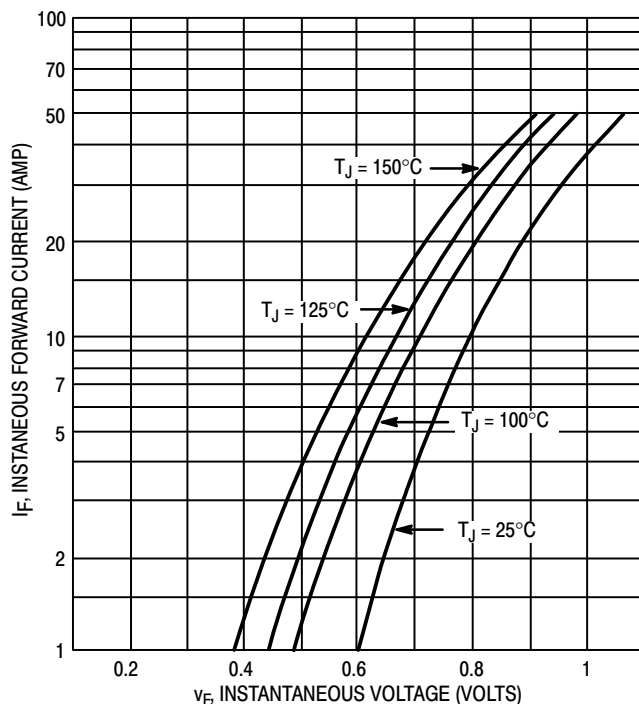


Figure 1. Typical Forward Voltage (Per Leg)

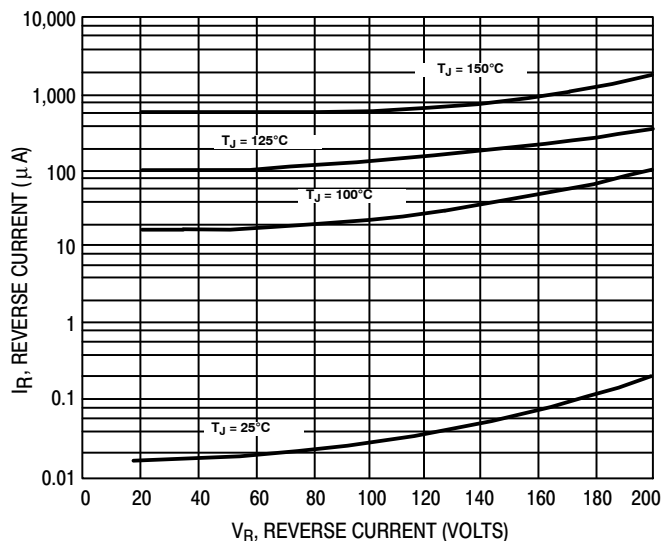


Figure 2. Typical Reverse Current (Per Leg)

MBRF20200CTG

TEST CONDITION FOR ISOLATION TEST*

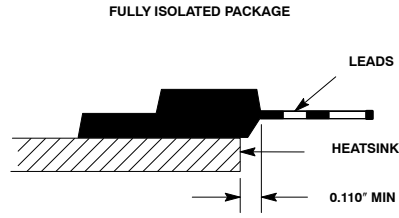
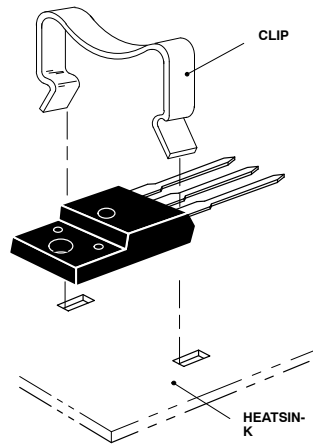


Figure 3. Mounting Position

*Measurement made between leads and heatsink with all leads shorted together.

MOUNTING INFORMATION



Clip-Mounted

Figure 4. Typical Mounting Technique

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

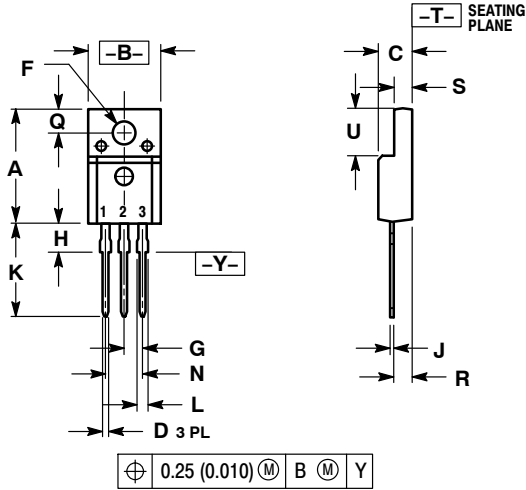
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SCALE 1:1

TO-220 FULLPAK CASE 221D-03 ISSUE K

DATE 27 FEB 2009



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH
 3. 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

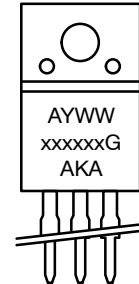
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.617	0.635	15.67	16.12
B	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
H	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

MARKING DIAGRAMS

- | | | |
|--|---|--|
| STYLE 1:
PIN 1. GATE
2. DRAIN
3. SOURCE | STYLE 2:
PIN 1. BASE
2. COLLECTOR
3. EMITTER | STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE |
| STYLE 4:
PIN 1. CATHODE
2. ANODE
3. CATHODE | STYLE 5:
PIN 1. CATHODE
2. ANODE
3. GATE | STYLE 6:
PIN 1. MT 1
2. MT 2
3. GATE |



Bipolar



Rectifier

- | | |
|-------------------------------|---------------------------|
| xxxxxx = Specific Device Code | A = Assembly Location |
| G = Pb-Free Package | Y = Year |
| A = Assembly Location | WW = Work Week |
| Y = Year | xxxxxx = Device Code |
| WW = Work Week | G = Pb-Free Package |
| | AKA = Polarity Designator |

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